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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f091rct6u

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SWCLK SWDIO as AF POWER Serial Wire Debug VOLT.REG $V_{DD} = 2 \text{ to } 3.6 \text{ V}$ 3.3 V to 1.8 V Obl Flash Or memory interface Flash GPL up to 256 KB 32-bit CORTEX-M0 CPU OKIN ← SUPPLY SUPERVISION $f_{MAX} = 48 \text{ MHz}$ V_{DDIO2} OKIN ◀ NRST SRAM 32 KB SRAM controller matri Reset ◀ V_{DDA} POR/PDR Int ◀ V_{SSA} NVIC @ V_{DDA} V_{DD} Bus HSI14 RC 14 MHz PVD HSI RC 8 MHz @ V_{DDA} PLLCLK @ V_{DD} LSI GP DMA RC 40 kHz XTAL OSC OSC_IN 12 channels HSI48 4-32 MHz RC 48MHz Ind. Window WDG PA[15:0] GPIO port A RESET & CLOCK ₹. CONTROL V_{BAT} = 1.65 to 3.6 V PB[15:0] GPIO port B OSC32_IN OSC32_OUT PC[15:0] GPIO port C System and peripheral XTAL32 kHz clocks PD[15:0] GPIO port D 3 TAMPER-RTC RTC AHB reg (ALARM OUT) PE[15:0] GPIO port E RTC interface PF[10:9], PF6 PF[3:0] Щ GPIO port F CRS SYNC 4 channels 3 compl. channels BRK, ETR input as AF PWM TIMER 1 CRC PAD 8 groups of 4 channels 4 ch., ETR as AF TIMER 2 32-bit Sensing Controller switches AHB TIMER 3 4 ch., ETR as AF SYNC APR TIMER 14 1 channel as AF EXT. IT WKUP 88 AF [2 channels 1 compl, BRK as AF TIMER 15 SRAM 1 channel 1 compl, BRK as AF 256 B TIMER 16 į į 1 channel 1 compl, BRK as AF IR_OUT as AF TIMER 17 TX, RX as AF **BxCAN** Window WDG RX, TX,CTS, RTS, CK as AF USART1 MOSI/SD SPI1/I2S1 MISO/MCK SCK/CK NSS/WS as AF RX, TX,CTS, RTS, CK as AF USART2 DBGMCU RX, TX,CTS, RTS, CK as AF USART3 MOSI/SD SPI2/I2S2 RX, TX,CTS, RTS, CK as AF USART4 SCK/CK NSS/WS as AF SYSCFG IF USART5 RX, TX, RTS, CK as AF USART6 RX, TX, RTS, CK as AF INPUT + GP comparator 1 USART7 RX, TX, RTS, CK as AF OUTPUT GP comparator 2 USART8 RX, TX, RTS, CK as AF as AF @ V_{DDA} SCL, SDA, SMBA (20 mA FM+) as AF I2C1 Temp. SCL, SDA (20 mA FM+) as AF I2C2 16x AD input IF 12-bit ADC CEC as AF HDMI-CEC TIMER 6 12-bit DAC ►DAC OUT1 V_{DDA} V_{SSA} TIMER 7 @ V_{DDA} 12-bit DAC ► DAC_OUT2 @ V_{DDA} Power domain of analog blocks: V_{BAT} V_{DD} V_{DDA} MSv34957V2

Figure 1. Block diagram



3 Functional overview

Figure 1 shows the general block diagram of the STM32F091xB/xC devices.

3.1 ARM®-Cortex®-M0 core

The ARM[®] Cortex[®]-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM[®] Cortex[®]-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F091xB/xC devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 32 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
 - up to 256 Kbytes of embedded Flash memory for programs and data
 - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex[®]-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bits are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot pin is shared with the standard GPIO and can be disabled through the boot selector option bits. The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15 or PA9/PA10 or I²C on pins PB6/PB7.



TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate with TIM1 via the Timer Link feature for synchronization or event chaining.

TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

3.14.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.14.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- maskable system interrupt generation when the counter reaches 0
- programmable clock source (HCLK or HCLK/8)

3.15 Real-time clock (RTC) and backup registers

The RTC and the five backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, or at wake up from Standby mode.

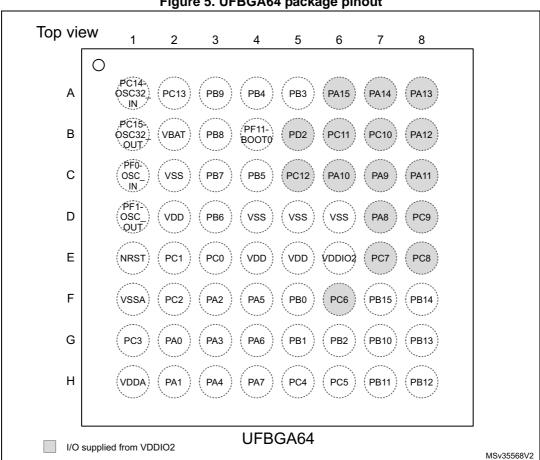


Figure 5. UFBGA64 package pinout

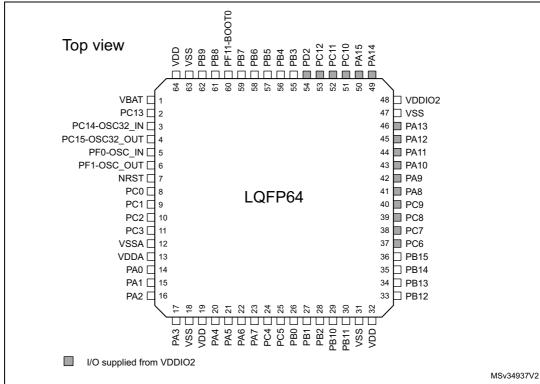


Figure 6. LQFP64 package pinout



Table 13. STM32F091xB/xC pin definitions (continued)

	Pi	n nui	mber	s						Pin functions		
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
J1	19	-	-	-	-	PF2	I/O	FT		EVENTOUT, USART7_TX, USART7_CK_RTS	WKUP8	
K1	20	F1	12	G8	8	VSSA	S	-		Analog grou	nd	
M1	21	H1	13	Н8	9	VDDA	S	ı		Analog power s	upply	
L1	22	-	-	-	-	PF3	I/O	FT		EVENTOUT, USART7_RX, USART6_CK_RTS		
L2	23	G2	14	F7	10	PA0	I/O	ТТа		USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1, USART4_TX COMP1_OUT	RTC_TAMP2, WKUP1, ADC_IN0, COMP1_INM6	
M2	24	H2	15	F6	11	PA1	I/O	ТТа		USART2_RTS, TIM2_CH2, TIM15_CH1N, TSC_G1_IO2, USART4_RX, EVENTOUT	ADC_IN1, COMP1_INP	
K3	25	F3	16	E5	12	PA2	I/O	ТТа		USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3 COMP2_OUT	ADC_IN2, WKUP4, COMP2_INM6	
L3	26	G3	17	H7	13	PA3	I/O	TTa		USART2_RX,TIM2_CH4, TIM15_CH2, TSC_G1_IO4	ADC_IN3, COMP2_INP	
D3	27	C2	18	G7	-	VSS	S	-		Ground		
Н3	28	D2	19	G6	-	VDD	S	-		Digital power s	upply	
М3	29	Н3	20	H6	14	PA4	I/O	ТТа		SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK, USART6_TX	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT1	
K4	30	F4	21	F5	15	PA5	I/O	ТТа		SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2, USART6_RX	COMP1_INM5, COMP2_INM5, ADC_IN5, DAC_OUT2	



Table 13. STM32F091xB/xC pin definitions (continued)

	Pi	n nui	mber	s						Pin functions		
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
L4	31	G4	22	G5	16	PA6	I/O	ТТа		SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT, USART3_CTS	ADC_IN6	
M4	32	H4	23	E4	17	PA7	I/O	ТТа		SPI1_MOSI, I2S1_SD, TIM3_CH2, TIM14_CH1, TIM1_CH1N, TIM17_CH1, COMP2_OUT, TSC_G2_IO4, EVENTOUT	ADC_IN7	
K5	33	H5	24	H5	-	PC4	I/O	TTa		EVENTOUT, USART3_TX	ADC_IN14	
L5	34	H6	25	F4	-	PC5	I/O	TTa		TSC_G3_IO1, USART3_RX	ADC_IN15, WKUP5	
M5	35	F5	26	G4	18	PB0	I/O	ТТа		TIM3_CH3, TIM1_CH2N, TSC_G3_IO2, EVENTOUT, USART3_CK	ADC_IN8	
M6	36	G5	27	F3	19	PB1	I/O	ТТа		TIM3_CH4, USART3_RTS, TIM14_CH1, TIM1_CH3N, TSC_G3_IO3	ADC_IN9	
L6	37	G6	28	H4	20	PB2	I/O	FT		TSC_G3_IO4	-	
M7	38	-	-	-	-	PE7	I/O	FT		TIM1_ETR, USART5_CK_RTS	-	
L7	39	-	-	-	-	PE8	I/O	FT		TIM1_CH1N, USART4_TX	-	
M8	40	-	-	-	-	PE9	I/O	FT		TIM1_CH1, USART4_RX	<u>-</u>	
L8	41	-	-	-	-	PE10	I/O	FT		TIM1_CH2N, USART5_TX	-	
M9	42	-	-	-	-	PE11	I/O	FT		TIM1_CH2, USART5_RX	-	
L9	43	-	-	-	-	PE12	I/O	FT		SPI1_NSS, I2S1_WS, TIM1_CH3N	-	
M10	44	-	-	-	-	PE13	I/O	FT		SPI1_SCK, I2S1_CK, TIM1_CH3	-	

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Table 18. Alternate functions selected through GPIOE_AFR registers for port E

Pin name	AF0	AF1
PE0	TIM16_CH1	EVENTOUT
PE1	TIM17_CH1	EVENTOUT
PE2	TIM3_ETR	TSC_G7_IO1
PE3	TIM3_CH1	TSC_G7_IO2
PE4	TIM3_CH2	TSC_G7_IO3
PE5	TIM3_CH3	TSC_G7_IO4
PE6	TIM3_CH4	-
PE7	TIM1_ETR	USART5_CK_RTS
PE8	TIM1_CH1N	USART4_TX
PE9	TIM1_CH1	USART4_RX
PE10	TIM1_CH2N	USART5_TX
PE11	TIM1_CH2	USART5_RX
PE12	TIM1_CH3N	SPI1_NSS, I2S1_WS
PE13	TIM1_CH3	SPI1_SCK, I2S1_CK
PE14	TIM1_CH4	SPI1_MISO, I2S1_MCK
PE15	TIM1_BKIN	SPI1_MOSI, I2S1_SD

Table 19. Alternate functions selected through GPIOF_AFR registers for port F

Pin name	AF0	AF1	AF2
PF0	CRS_SYNC	I2C1_SDA	-
PF1	-	I2C1_SCL	-
PF2	EVENTOUT	USART7_TX	USART7_CK_RTS
PF3	EVENTOUT	USART7_RX	USART6_CK_RTS
PF6	-	-	-
PF9	TIM15_CH1	USART6_TX	-
PF10	TIM15_CH2	USART6_RX	-

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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 21: Voltage characteristics*, *Table 22: Current characteristics* and *Table 23: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 21. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit
V_{DD} – V_{SS}	External main supply voltage	- 0.3	4.0	V
V _{DDIO2} -V _{SS}	External I/O supply voltage	- 0.3	4.0	V
V _{DDA} -V _{SS}	External analog supply voltage	- 0.3	4.0	V
V _{DD} –V _{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V _{BAT} -V _{SS}	External backup supply voltage	- 0.3	4.0	V
	Input voltage on FT and FTf pins	V _{SS} - 0.3	V _{DDIOx} + 4.0 ⁽³⁾	٧
$V_{IN}^{(2)}$	Input voltage on TTa pins	V _{SS} - 0.3	4.0	V
	Input voltage on any other pin	V _{SS} - 0.3	4.0	V
$ \Delta V_{DDx} $	Variations between different V _{DD} power pins	-	50	mV
V _{SSx} - V _{SS}	Variations between all the different ground pins	-	50	mV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3 sensitivity chara		-

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

^{2.} V_{IN} maximum must always be respected. Refer to for the maximum allowed injected current values.

^{3.} Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency:
 - 0 wait state and Prefetch OFF from 0 to 24 MHz
 - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled f_{PCLK} = f_{HCLK}

The parameters given in *Table 29* to *Table 32* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.



trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution:

Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 35: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

 I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_{S}$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



6.3.6 Wakeup time from low-power mode

The wakeup times given in *Table 36* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop or Standby mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode. The wakeup source from Standby mode is the WKUP1 pin (PA0).

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Symbol	Parameter	Conditions		Тур	@ V DD = \	/DDA		Max	Unit
	rarameter	Conditions	= 2.0 V	= 2.4 V	= 2.7 V	= 3 V	= 3.3 V	IVIAX	Onic
t	Wakeup from Stop	Regulator in run mode	3.2	3.1	2.9	2.9	2.8	5	
twustop	mode	Regulator in low power mode	7.0	5.8	5.2	4.9	4.6	9	ue
t _{WUSTANDBY}	Wakeup from Standby mode	-	60.4	55.6	53.5	52	51	-	μs
t _{WUSLEEP}	Wakeup from Sleep mode	-		4 SY	SCLK cy	cles		-	

Table 36. Low-power mode wakeup timings

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 15: High-speed external clock source AC timing diagram*.

Table 37. High-speed external user clock characteristics

Symbol	Parameter ⁽¹⁾	Min	Тур	Max	Unit
f _{HSE_ext}	User external clock source frequency	-	8	32	MHz
V _{HSEH}	OSC_IN input pin high level voltage	0.7 V _{DDIOx}	ı	V_{DDIOx}	V
V _{HSEL}	OSC_IN input pin low level voltage	V_{SS}	-	0.3 V _{DDIOx}	V
$t_{w(HSEH)} \ t_{w(HSEL)}$	OSC_IN high or low time	15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time	-	-	20	113



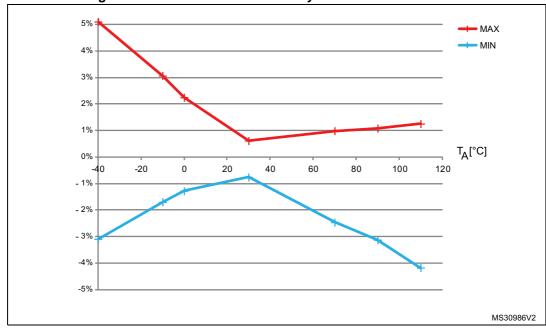
High-speed internal 14 MHz (HSI14) RC oscillator (dedicated to ADC)

Table 42. HSI14 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI14}	Frequency	-	-	14	-	MHz
TRIM	HSI14 user-trimming step	-	-	-	1 ⁽²⁾	%
DuCy _(HSI14)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%
		$T_A = -40 \text{ to } 105 ^{\circ}\text{C}$	-4.2 ⁽³⁾	-	5.1 ⁽³⁾	%
ACC	Accuracy of the HSI14	T _A = -10 to 85 °C	$-3.2^{(3)}$	-	3.1 ⁽³⁾	%
ACC _{HSI14}	oscillator (factory calibrated)	T _A = 0 to 70 °C	-2.5 ⁽³⁾	-	2.3 ⁽³⁾	%
		T _A = 25 °C	-1	-	1	%
t _{su(HSI14)}	HSI14 oscillator startup time	-	1 ⁽²⁾	-	2 ⁽²⁾	μs
I _{DDA(HSI14)}	HSI14 oscillator power consumption	-	-	100	150 ⁽²⁾	μΑ

- 1. V_{DDA} = 3.3 V, T_{A} = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.

Figure 20. HSI14 oscillator accuracy characterization results



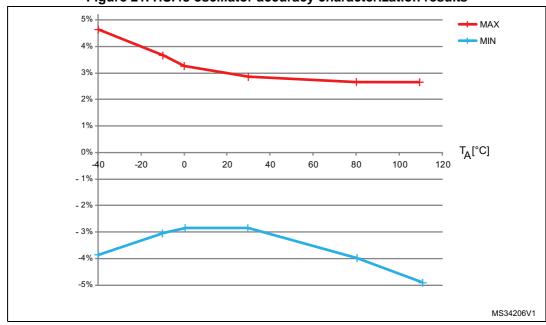
High-speed internal 48 MHz (HSI48) RC oscillator

Table 43. HSI48 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI48}	Frequency	-	-	48	-	MHz
TRIM	HSI48 user-trimming step	-	0.09 ⁽²⁾	0.14	0.2 ⁽²⁾	%
DuCy _(HSI48)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%
		$T_A = -40 \text{ to } 105 ^{\circ}\text{C}$	-4.9 ⁽³⁾	-	4.7 ⁽³⁾	%
ACC	Accuracy of the HSI48	$T_A = -10 \text{ to } 85 ^{\circ}\text{C}$	-4.1 ⁽³⁾	-	3.7 ⁽³⁾	%
ACC _{HSI48}	oscillator (factory calibrated)	T _A = 0 to 70 °C	-3.8 ⁽³⁾	-	3.4 ⁽³⁾	%
		T _A = 25 °C	-2.8	-	2.9	%
t _{su(HSI48)}	HSI48 oscillator startup time	-	-	-	6 ⁽²⁾	μs
I _{DDA(HSI48)}	HSI48 oscillator power consumption	-	-	312	350 ⁽²⁾	μА

- 1. V_{DDA} = 3.3 V, T_{A} = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.

Figure 21. HSI48 oscillator accuracy characterization results



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Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOX}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 21: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see Table 21: Voltage characteristics).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 54. Output voltage characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL}	Output low level voltage for an I/O pin	CMOS port ⁽²⁾	-	0.4	.,
V _{OH}	Output high level voltage for an I/O pin	$ I_{IO} = 8 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	V _{DDIOx} -0.4	-	V
V _{OL}	Output low level voltage for an I/O pin	TTL port ⁽²⁾	-	0.4	.,
V _{OH}	Output high level voltage for an I/O pin	I _{IO} = 8 mA V _{DDIOx} ≥ 2.7 V	2.4	-	V
V _{OL} ⁽³⁾	Output low level voltage for an I/O pin	I _{IO} = 20 mA	-	1.3	V
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin	V _{DDIOx} ≥ 2.7 V	V _{DDIOx} -1.3	-	
V _{OL} ⁽³⁾	Output low level voltage for an I/O pin	I _{IO} = 6 mA	-	0.4	
V _{OH} ⁽³⁾	Output high level voltage for an I/O pin	V _{DDIOx} ≥ 2 V	V _{DDIOx} -0.4	-	V
V _{OL} ⁽⁴⁾	Output low level voltage for an I/O pin	II I = 4 mA	-	0.4	V
V _{OH} ⁽⁴⁾	Output high level voltage for an I/O pin	I _{IO} = 4 mA	V _{DDIOx} -0.4	-	V
V _{OLFm+} ⁽³⁾	Output low level voltage for an FTf I/O pin in Fm+ mode	$ I_{IO} = 20 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	-	0.4	V
	Triii+ mode	I _{IO} = 10 mA	-	0.4	V

The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in Table 21:
 Voltage characteristics, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.

- 2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
- 3. Data based on characterization results. Not tested in production.
- 4. Data based on characterization results. Not tested in production.

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Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

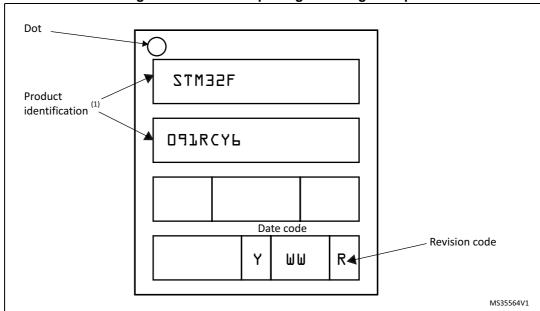


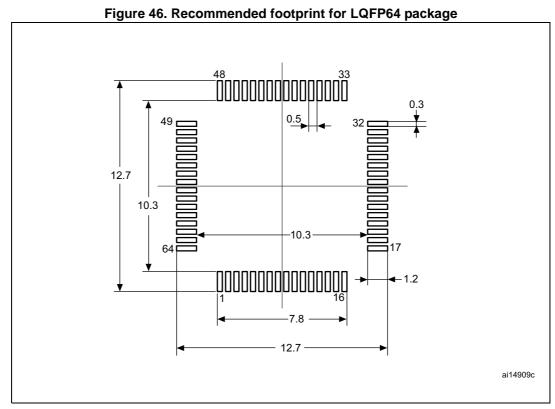
Figure 44. WLCSP64 package marking example

Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

inches⁽¹⁾ millimeters **Symbol** Min Тур Max Min Тур Max 7.500 0.2953 E3 0.500 0.0197 е 0° 7° 0° 7° Κ 3.5° 3.5° L 0.450 0.600 0.750 0.0177 0.0236 0.0295 L1 1.000 0.0394 0.080 0.0031 CCC

Table 77. LQFP64 package mechanical data (continued)

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.



1. Dimensions are expressed in millimeters.

7.7 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7x7 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

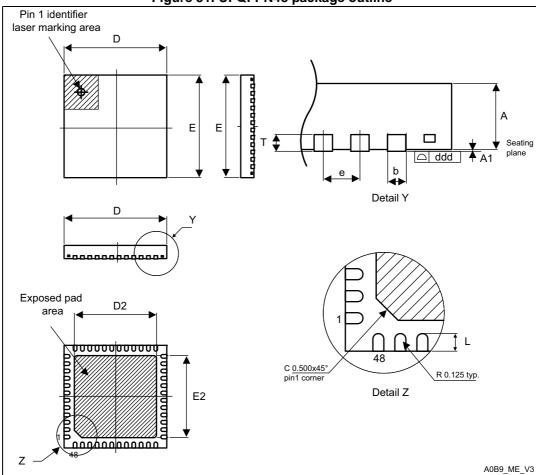


Figure 51. UFQFPN48 package outline

- 1. Drawing is not to scale.
- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

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Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

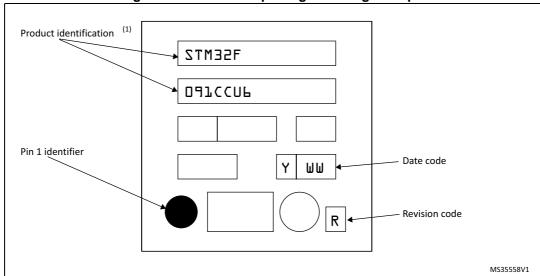


Figure 53. UFQFPN48 package marking example

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

